Recognizes, on an annual basis, the most significant contribution in a paper published in the IEEE Transactions on Terahertz Science and Technology.

Maris Bauer, Adam Ramer, Serguei A. Chevtchenko, Konstantin Y. Osipov, Dovile Cibiraite, Sandra Pralgauskaite, Kestutis Ikamas, Alvydas Lisauskas, Wolfgang Heinrich, Viktor Krozer, Hartmut G. Roskos, for their paper "A High-Sensitivity AlGaN/GaN HEMT Terahertz Detector With Integrated Broadband Bow-Tie Antenna," in IEEE Transactions on Terahertz Science and Technology, Vol. 9, Issue. 4, pp. 430-444, July 2019.



#### **Maris Bauer**

Maris Bauer was born in Frankfurt am Main, Germany, in 1985. He received the doctoral degree in physics from Goethe University Frankfurt, Germany, in 2018 in the group of Prof. Dr. Hartmut Roskos, on the modeling of charge carrier transport and photo-thermoelectric effects in field-effect transistors for terahertz detection, and their practical implementation in various material systems such as carbon-based materials and III-V semiconductors. From 2008 to 2014, he was a Research Assistant with SynView GmbH. In 2017, he joined the Department of Materials Characterization and Testing at Fraunhofer ITWM, Germany, currently working on terahertz applications and system design.



#### **Adam Rämer**

Adam Rämer received the Dipl.-Ing. degree in electrical engineering from the Technical University of Berlin, Germany, in 2012. Since 2012 he has been a Research Associate with the Joint Lab THz Components and Systems of Ferdinand-Braun-Institut (FBH), Berlin, Germany. There, he is involved in the development and design of GaN HEMT-based broadband THz detectors. His research interests are the fields of power amplifiers, broadband antennas, GaN HEMTs for special applications, MMIC design and THz measurement.

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#### **Kestutis Ikamas**

Kestutis Ikamas received the Diploma in physics in 1995 and the doctorate degree working on the modeling of broadband THz detectors with field-effect transistors and the application of these devices for systems with pulsed and dc sources, in 2018, from Vilnius University, Vilnius, Lithuania. He is currently with the Noise and Terahertz Electronics Group, Vilnius University, where he is involved in the area of CMOS transistor-based terahertz detectors' and sources' design, modeling, and application.



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Alvydas Lisauskas (M'18) received the Diploma in physics from Vilnius University, Lithuania, in 1995, and the Ph.D. degree from Royal Institute of Technology, Stockholm, Sweden, in 2001. From 2002 till 2013 he was with the Ultrafast Spectroscopy and Terahertz Physics Group, Goethe University Frankfurt, Germany, working on novel semiconductor devices for THz applications. Since 2014, he is Professor at Vilnius University. Since February 2019, he is also a Group Leader on Terahertz Electronics with the CENTERA Labs, Institute of High Pressure Physics PAS, Warsaw, Poland. His research interests include terahertz electronics, design and modelling of semiconductor devices, and terahertz imaging techniques.

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Wolfgang Heinrich received the PhD and Habilitation degrees in 1987 and 1992, respectively, from the Technical University of Darmstadt, Darmstadt, Germany. Since 1993, he has been with the Ferdinand-Braun-Institut (FBH) at Berlin, Germany, where he is the Head of the Microwave Department and the Deputy Director of the institute. Since 2008, he has been also Professor with the Technical University of Berlin. He has authored or coauthored more than 400 peer-reviewed publications and conference contributions. His present research interests include MMIC design with an emphasis on GaN power amplifiers, mm-wave and sub-mmwave integrated circuits and packaging, and electromagnetic simulation.



#### **Viktor Krozer**

Viktor Krozer (M'91 - SM'03) received the Dipl.-Ing. and Dr.-Ing. degree in electrical engineering at the Technical University Darmstadt in 1984 and in 1991, respectively. In 1991 he became senior scientist at the TU Darmstadt working on high-temperature microwave devices and circuits and submillimeter-wave electronics. From 1996–2002 Dr. Krozer was professor at the Technical University of Chemnitz, Germany. During 2002-2009 Dr. Krozer was professor at Electromagnetic Systems, DTU Elektro, Technical University of Denmark, and was heading the Microwave Technology Group. During 2009-2012 Dr. Krozer has been an endowed Oerlikon-Leibniz-Goethe professor for Terahertz Photonics at the Johann Wolfgang Goethe University Frankfurt, Germany and since 2012 heads the Goethe-Leibniz-Terahertz-Center at the same university. He is also with FBH Berlin, leading the THz components and systems group.

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